

<b>SANYO</b>	No.4134	<b>2SC4836</b>
	NPN Epitaxial Planar Silicon Transistor 20V/5A Switch Applications	

**Applications**

- Strobes, power supplies, relay drivers, lamp drivers.

**Features**

- Large allowable collector dissipation.
- Low saturation voltage.
- Large current capacity.
- Fast switching speed.
- Usage of radial taping to meet automatic mounting.

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector-to-Base Voltage	V <sub>CB0</sub>	60	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-to-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	I <sub>C</sub>	5	A
Peak Collector Current	i <sub>cp</sub>	8	A
Collector Dissipation	P <sub>C</sub>	1.5	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0			100	nA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			100	nA
DC Current Gain	h <sub>FE</sub> (1)	V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA	120	※	560	※
	h <sub>FE</sub> (2)	V <sub>CE</sub> = 2V, I <sub>C</sub> = 3A	95			
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA		120		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, f = 1MHz		45		pF

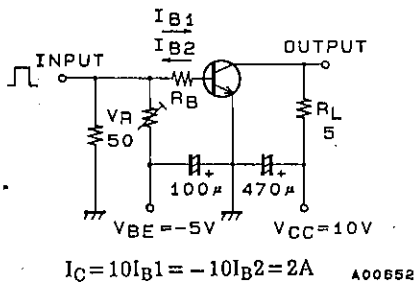
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※ : The 2SC4836 is classified by 500mA h<sub>FE</sub> as follows :

120 E 200	160 F 320	280 G 560
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**Switching Time Test Circuit**

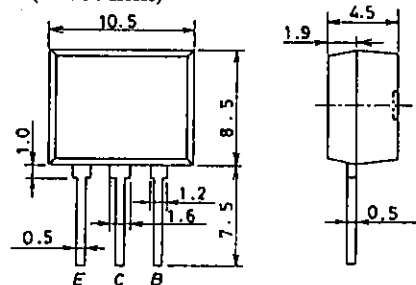
PW = 20μs  
DC ≤ 1%



Unit (resistance : Ω, capacitance : F)

**Package Dimensions 2084**

(unit : mm)

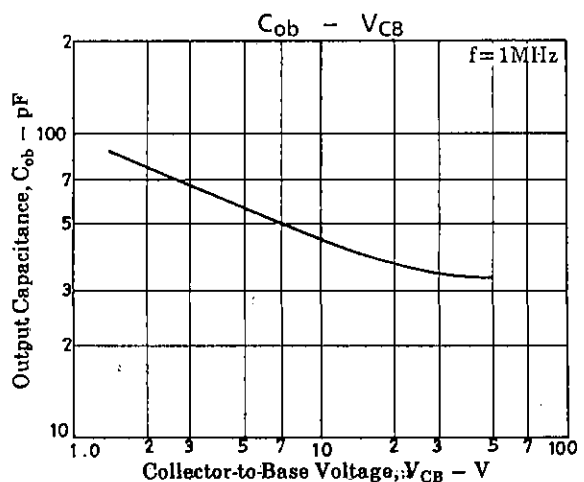
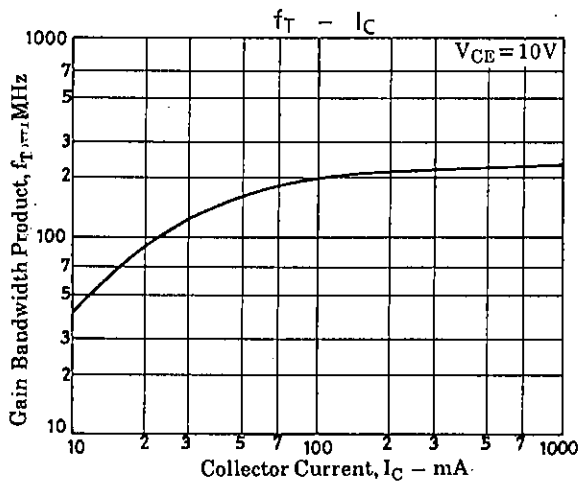
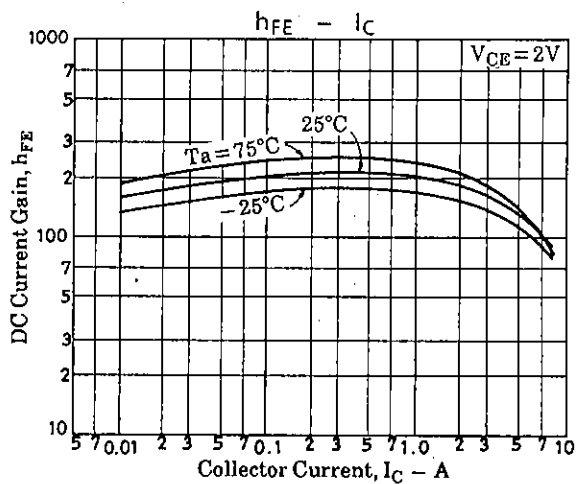
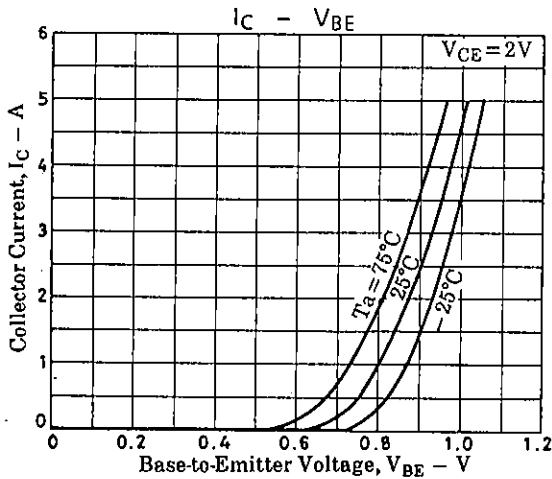
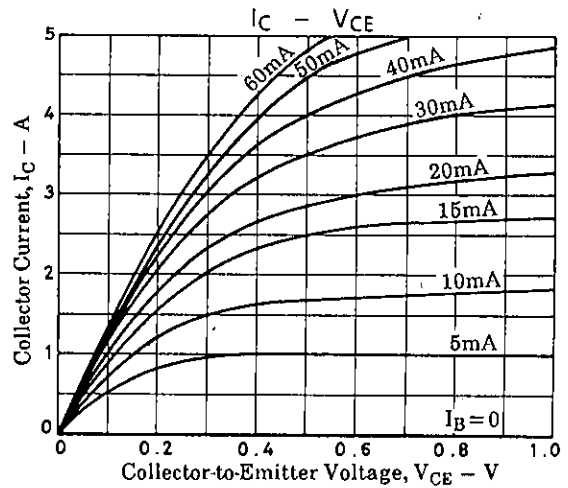
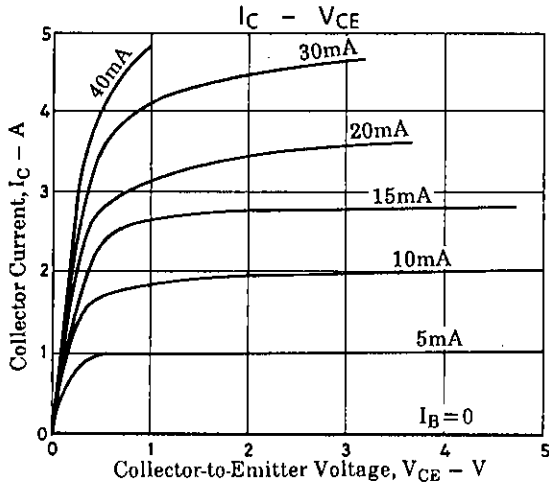


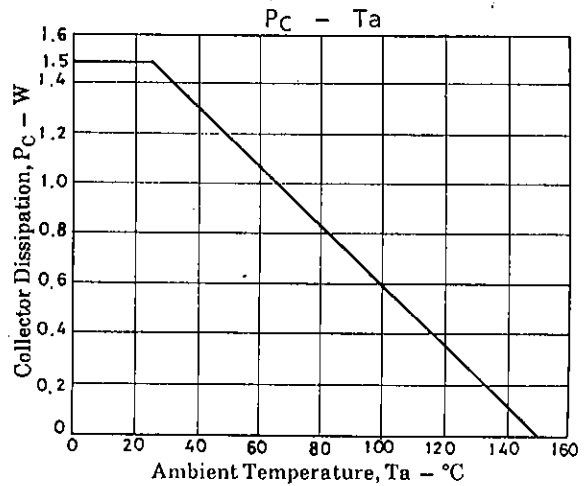
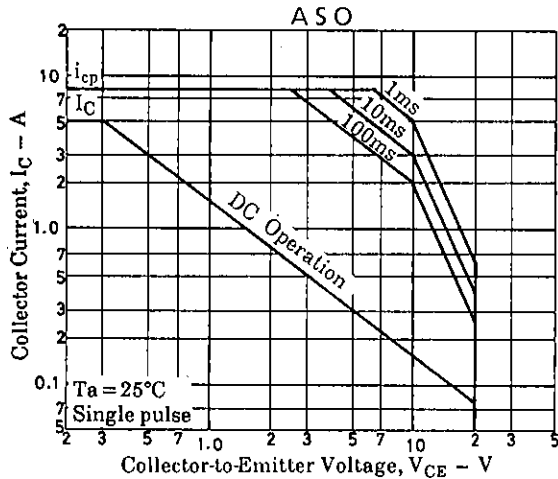
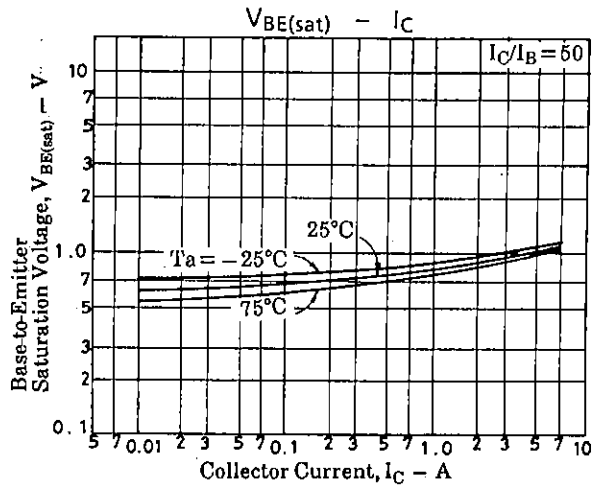
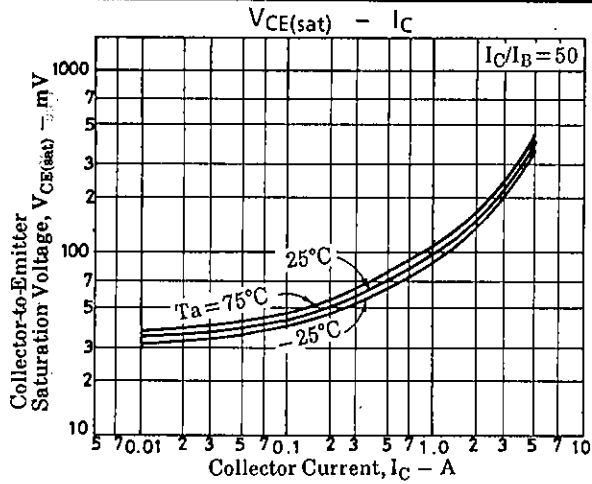
E : Emitter  
C : Collector  
B : Base

SANYO : FLP

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			min	typ	max	unit
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 60mA$		220	500	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 3A, I_B = 60mA$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6			V
Turn ON Time	$t_{on}$	See specified Test Circuit.		30		ns
Storage Time	$t_{stg}$	"		300		ns
Fall Time	$t_f$	"		40		ns





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